

Improving Porous Si Anode Properties by Atomic Layer Deposition (ALD) high-k Oxide Passivation For High Energy Density Storage Applications

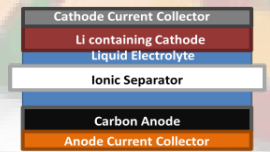
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Goal of this study:

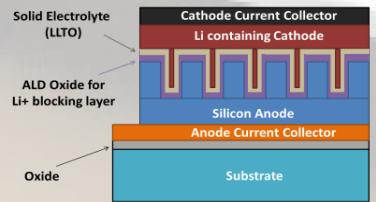
Design and fabricate high energy and high power density hybrid energy storage device for ASSIST platform

Current Battery Technology



- Liquid electrolyte is a safety concern when exposed to moisture
- Anode material has a low specific energy density $\sim 372 \text{ mAh g}^{-1}$
- Low power rate

Our Approach in ASSIST



3-Dimensional All Solid State Nanobatteries with Atomic Layer Deposition (ALD) Technique

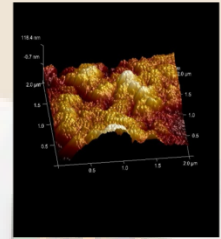
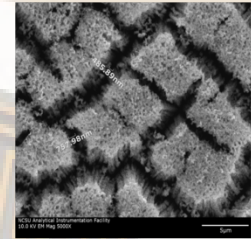
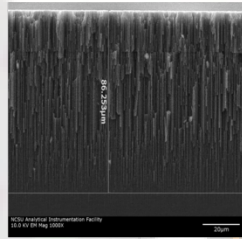
- All solid design
- Enhanced surface area to volume ratio
- Anode has high specific energy density $\sim 4200 \text{ mAhg}^{-1}$

- Advantages of ALD**
 - Conformal coverage
 - Complex structures may be used
 - Ensure mechanical and electrical stability at all interfaces
 - Safer packaging (no liquid/gel)
 - No need for separator to prevent electrode shorting
 - Precise thickness control

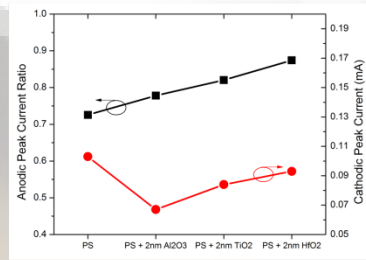
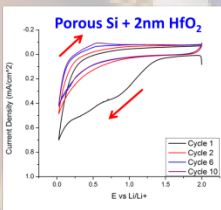
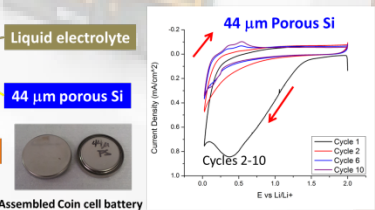
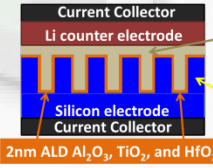
- Technology Impact**
 - All ALD based 3D SS energy storage will be a good candidate for high density energy storage device
 - It provides safe and stable operation (b/c there is no liquid electrolyte)

Porous Silicon Formation

- HF: H₂O₂: Ethanol: H₂O (9: 1: 4: 11)
- $i \cong 20 \text{ mA}$, $t = 10 \text{ min}$ to 30 min
- Porous layer depth $\cong 44 \mu\text{m}$ to $86 \mu\text{m}$
- Porosity $\sim 20\% \sim 60\%$
- Depth and porosity controlled by current and etching time



Structure and Cycling Characteristics



- Solid Electrolyte Interface formation from $\sim 0.4\text{V} - 1.4\text{V}$
- Lithiation peaks $\sim 0.4\text{V} - 0.5\text{V}$ cause Si amorphization, volumetric expansion, cracking
- Porous Si with ALD dielectrics demonstrate reduce lithiation peak i.e. less Si amorphization
- HfO₂ demonstrates highest capacity retention



NSF Nanosystems Engineering Research Center for Advanced Self-Powered Systems for Integrated Sensors and Technologies (ASSIST)

